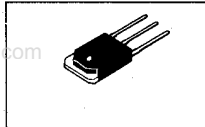




No.1222

**2SD1396**



NPN Triple Diffused Planar Type Silicon Transistor  
For Horizontal Output (Built-in Damper Diode)

**Features:**

- High Breakdown Voltage and High Reliability.
- High Switching Speed.
- Capable of being mounted easily due to one-point fixing type plastic mold package.

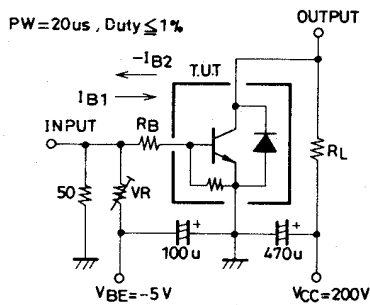
**Absolute Maximum Ratings at Ta=25°C**

			unit
Collector to Base Voltage	V <sub>CB0</sub>	1500	V
Collector to Emitter Voltage	V <sub>CE0</sub>	800	V
Emitter to Base Voltage	V <sub>EB0</sub>	7	V
Collector Current	I <sub>C</sub>	2.5	A
Peak Collector Current	i <sub>cp</sub>	10	A
Collector Dissipation	P <sub>C</sub>	T <sub>c</sub> =25°C 50	W
Junction Temperature	T <sub>j</sub>	150	°C
Storage Temperature	T <sub>stg</sub>	-55 to +150	°C

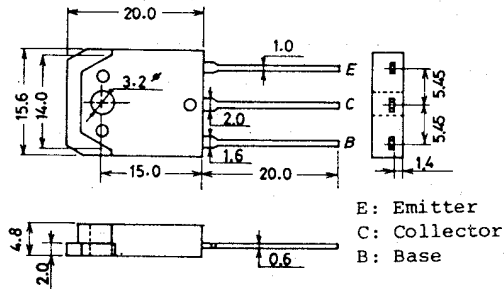
**Electrical Characteristics at Ta=25°C**

			min	typ	max	unit
Collector Cutoff Current	I <sub>CB0</sub>	V <sub>CB</sub> =800V, I <sub>E</sub> =0			10	uA
Emitter Cutoff Current	I <sub>EB0</sub>	V <sub>EB</sub> =4V, I <sub>C</sub> =0	40		130	mA
DC Current Gain	h <sub>FE</sub>	V <sub>CE</sub> =5V, I <sub>C</sub> =0.5A	8			
Gain Bandwidth Product	f <sub>T</sub>	V <sub>CE</sub> =10V, I <sub>C</sub> =0.5A		3		MHz
C-E Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =2A, I <sub>B</sub> =0.6A			8	V
B-E Saturation Voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =2A, I <sub>B</sub> =0.6A			1.5	V
C-B Breakdown Voltage	V(BR)CBO	I <sub>C</sub> =5mA, I <sub>E</sub> =0	1500			V
C-E Breakdown Voltage	V(BR)CEO	I <sub>C</sub> =100mA, R <sub>BE</sub> =∞	800			V
E-B Breakdown Voltage	V(BR)EBO	I <sub>E</sub> =200mA, I <sub>C</sub> =0	7			V
Diode Forward Voltage	V <sub>F</sub>	I <sub>EC</sub> =2.5A			2	V
Fall Time	t <sub>f</sub>	I <sub>C</sub> =2A, I <sub>B1</sub> =0.6A, I <sub>B2</sub> =-1.2A V <sub>CC</sub> =200V, R <sub>L</sub> =100ohm			0.7	us

**Switching Time Test Circuit**



**Case Outline 2022 (unit:mm)**



These specifications are subject to change without notice.